

FDN327N-VB Datasheet

SOT23-3 Single-N 20V Trench MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^e	Q_g (Typ.)
20	0.028 at $V_{GS} = 4.5$ V	6 ^a	8.8 nC
	0.042 at $V_{GS} = 2.5$ V	6 ^a	
	0.050 at $V_{GS} = 1.8$ V	5.6	

FEATURES

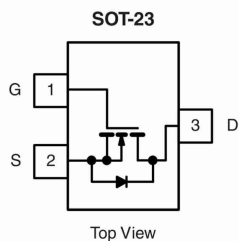
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- DC/DC Converters
- Load Switch for Portable Applications



ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$, unless otherwise noted				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	20	V
Gate-Source Voltage		V_{GS}	± 12	
Continuous Drain Current ($T_J = 150^\circ\text{C}$)	$T_C = 25^\circ\text{C}$	I_D	6 ^a	A
	$T_C = 70^\circ\text{C}$		5.1	
	$T_A = 25^\circ\text{C}$		5 ^{b, c}	
	$T_A = 70^\circ\text{C}$		4 ^{b, c}	
Pulsed Drain Current		I_{DM}	20	
Continuous Source-Drain Diode Current	$T_C = 25^\circ\text{C}$	I_S	1.75	W
	$T_A = 25^\circ\text{C}$		1.04 ^{b, c}	
Maximum Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	2.1	
	$T_C = 70^\circ\text{C}$		1.3	
	$T_A = 25^\circ\text{C}$		1.25 ^{b, c}	
	$T_A = 70^\circ\text{C}$		0.8 ^{b, c}	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	$^\circ\text{C}$
Soldering Recommendations (Peak Temperature)			260	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, d}	$t \leq 5$ s	R_{thJA}	80	100	$^\circ\text{C/W}$
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	40	60	

Notes:

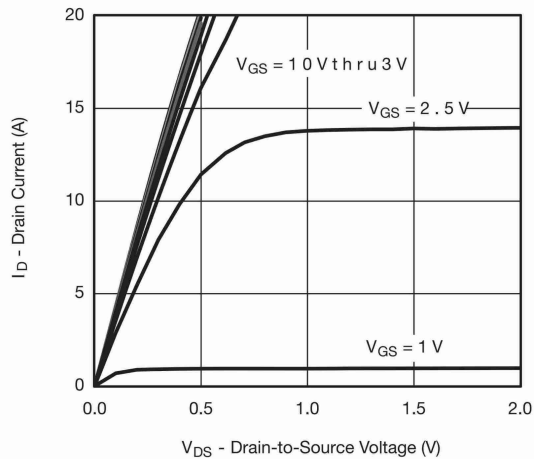
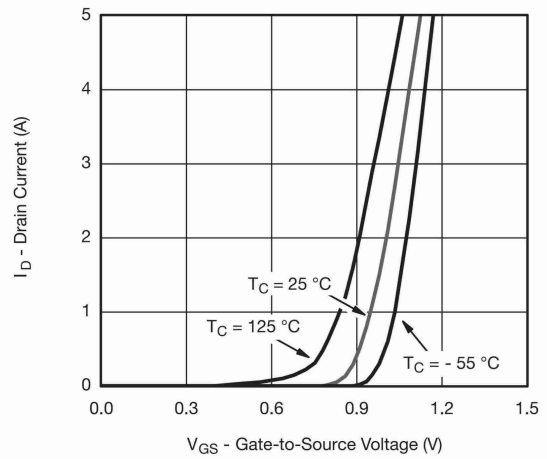
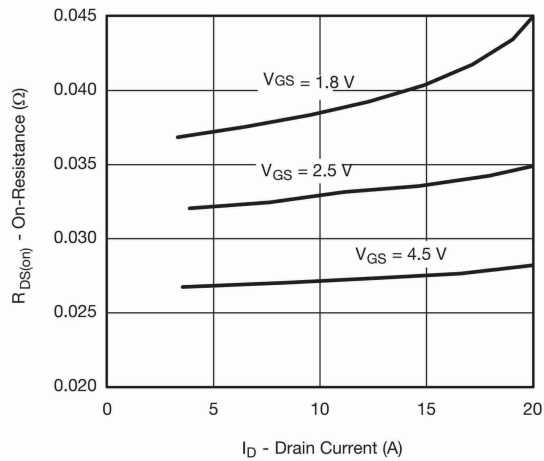
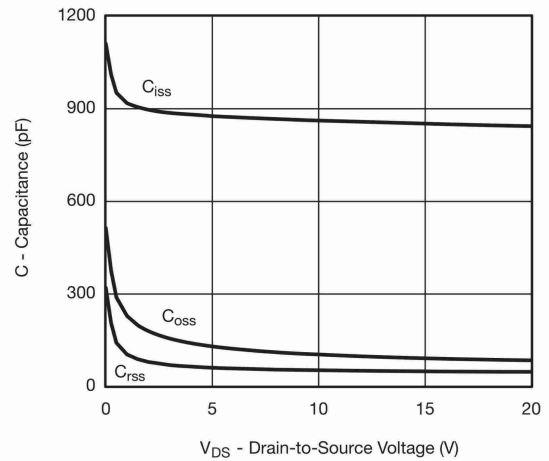
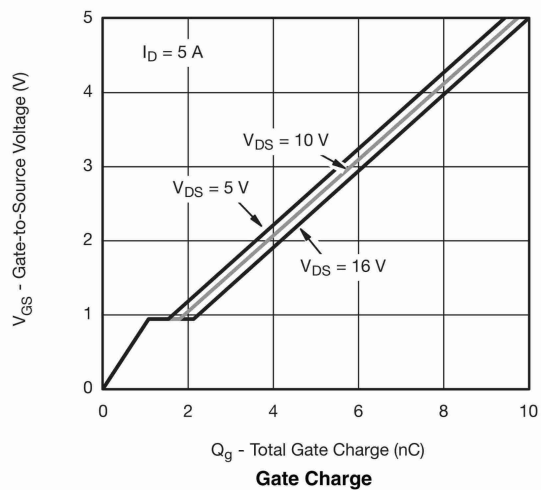
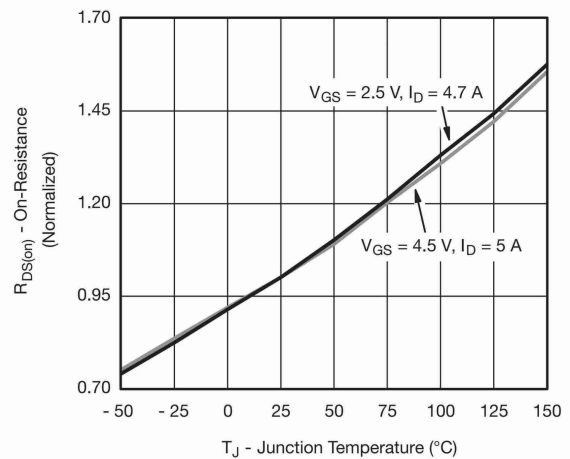
- Package limited
- Surface Mounted on 1" x 1" FR4 board.
- $t = 5$ s.
- Maximum under steady state conditions is 125 $^\circ\text{C/W}$.
- Based on $T_C = 25^\circ\text{C}$.

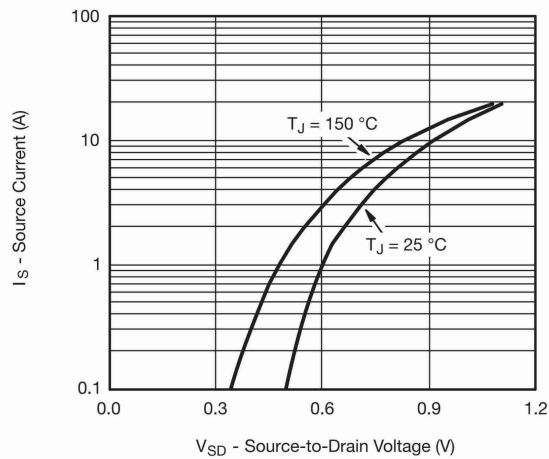
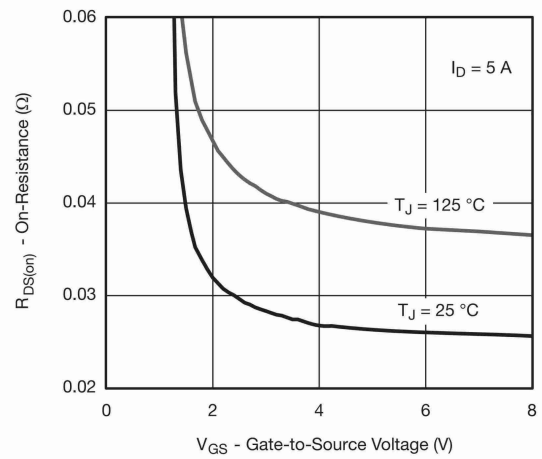
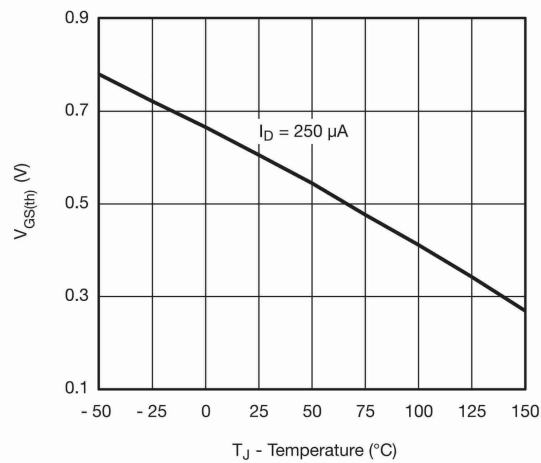
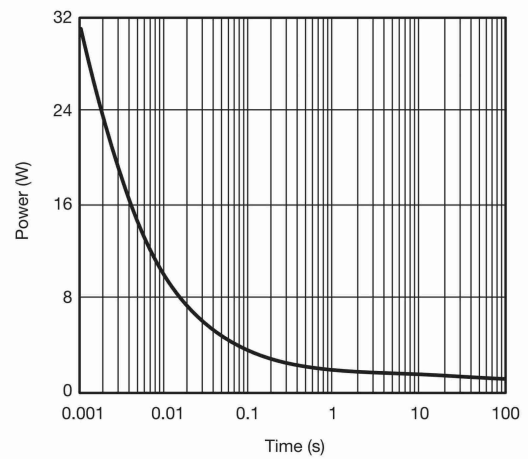
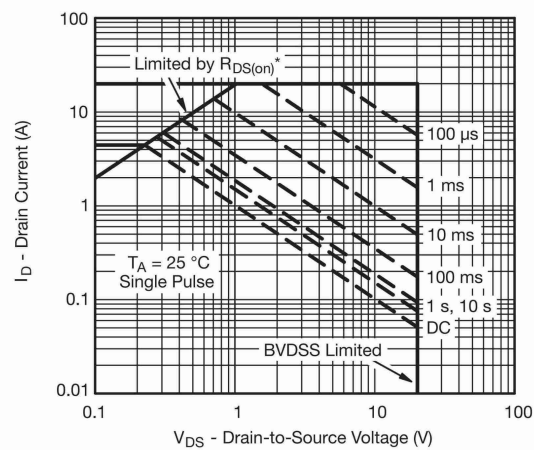
SPECIFICATIONS T _J = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	20			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA		25		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			- 2.6		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	0.45		1.0	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 8 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V			1	μA
		V _{DS} = 20 V, V _{GS} = 0 V, T _J = 70 °C			10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≤ 5 V, V _{GS} = 4.5 V	20			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 5.0 A		0.028		Ω
		V _{GS} = 2.5 V, I _D = 4.7 A		0.042		
		V _{GS} = 1.8 V, I _D = 4.3 A		0.050		
Forward Transconductance ^a	g _{fs}	V _{DS} = 10 V, I _D = 5.0 A		24		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz		865		pF
Output Capacitance	C _{oss}			105		
Reverse Transfer Capacitance	C _{rss}			55		
Total Gate Charge	Q _g	V _{DS} = 10 V, V _{GS} = 5 V, I _D = 5.0 A		12	18	nC
		V _{DS} = 10 V, V _{GS} = 4.5 V, I _D = 5.0 A		8.8	14	
Gate-Source Charge	Q _{gs}			1.1		
Gate-Drain Charge	Q _{gd}			0.7		
Gate Resistance	R _g	f = 1 MHz	0.5	2.4	4.8	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 10 V, R _L = 2.2 Ω I _D ≅ 4 A, V _{GEN} = 4.5 V, R _g = 1 Ω		8	16	ns
Rise Time	t _r			17	26	
Turn-Off Delay Time	t _{d(off)}			31	47	
Fall Time	t _f			8	16	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 10 V, R _L = 2.2 Ω I _D ≅ 4 A, V _{GEN} = 5 V, R _g = 1 Ω		5	10	
Rise Time	t _r			13	20	
Turn-Off Delay Time	t _{d(off)}			21	32	
Fall Time	t _f			6	12	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			1.75	A
Pulse Diode Forward Current	I _{SM}				20	
Body Diode Voltage	V _{SD}	I _S = 4 A, V _{GS} = 0 V		0.75	1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 4 A, dI/dt = 100 A/μs, T _J = 25 °C		12	20	ns
Body Diode Reverse Recovery Charge	Q _{rr}			5	10	nC
Reverse Recovery Fall Time	t _a			7		ns
Reverse Recovery Rise Time	t _b			5		

Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
 b. Guaranteed by design, not subject to production testing.

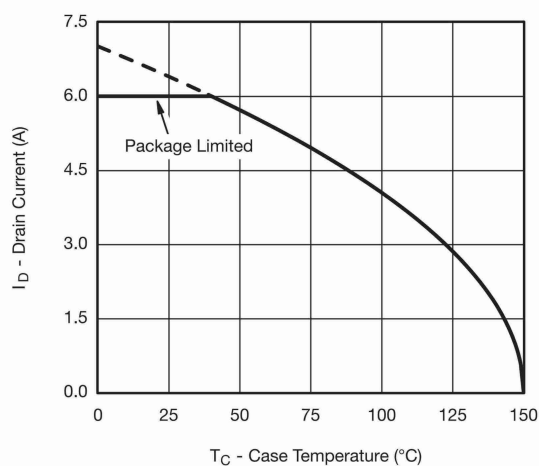
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

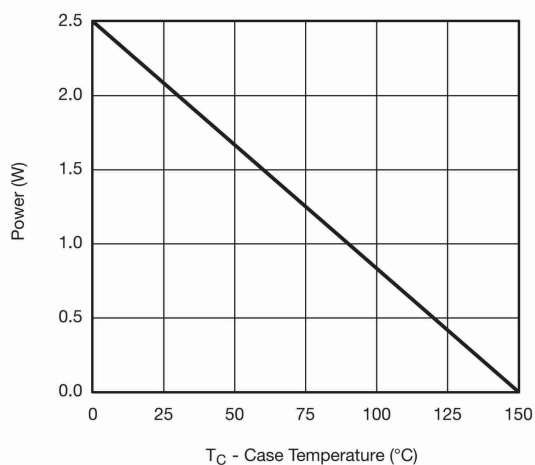
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Output Characteristics

Transfer Characteristics

On-Resistance vs. Drain Current and Gate Voltage

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature

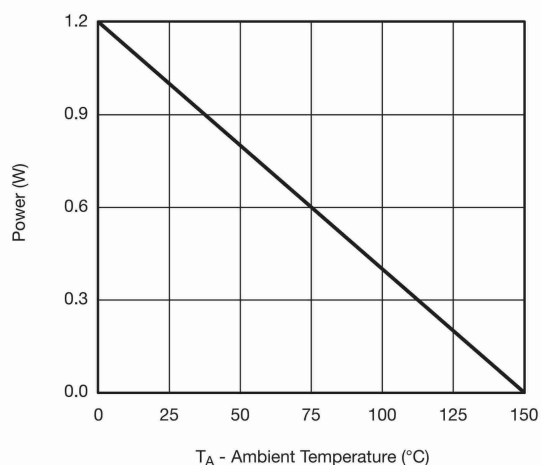
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Source-Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage

Single Pulse Power (Junction-to-Ambient)


* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

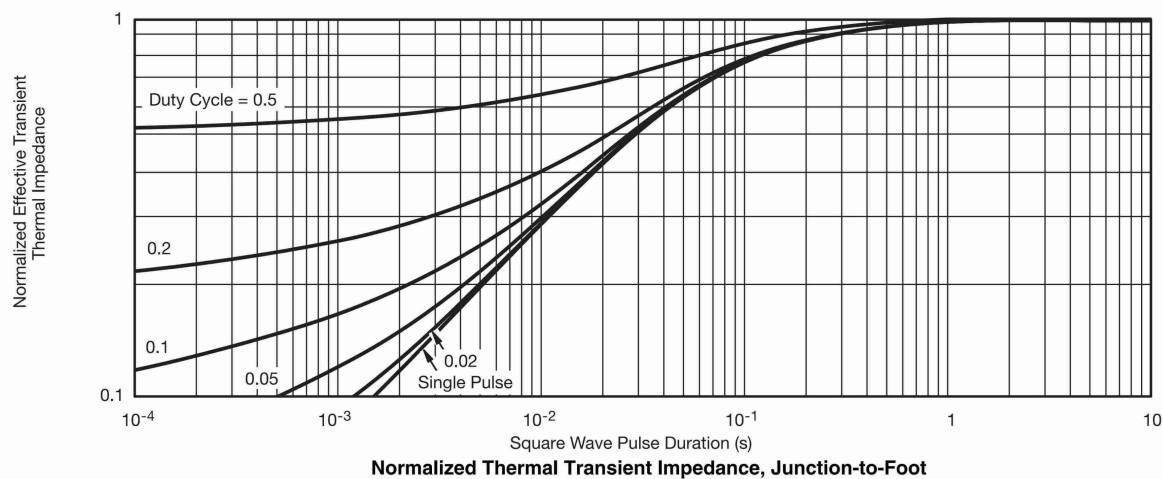
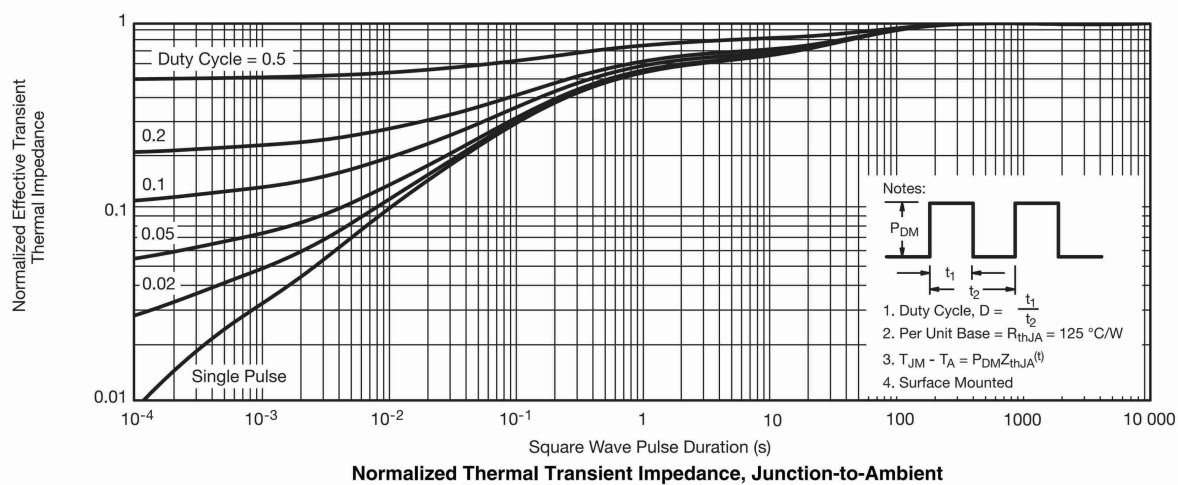
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

 T_C - Case Temperature (°C)

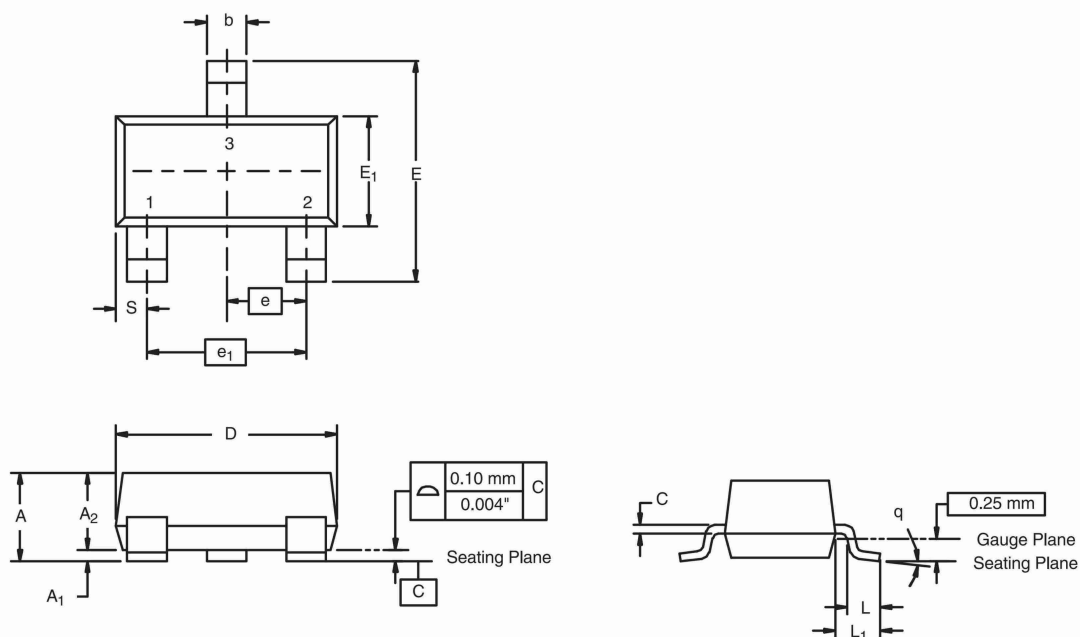
Current Derating*

 T_C - Case Temperature (°C)

Power Derating, Junction-to-Case

 T_A - Ambient Temperature (°C)

Power Derating, Junction-to-Ambient

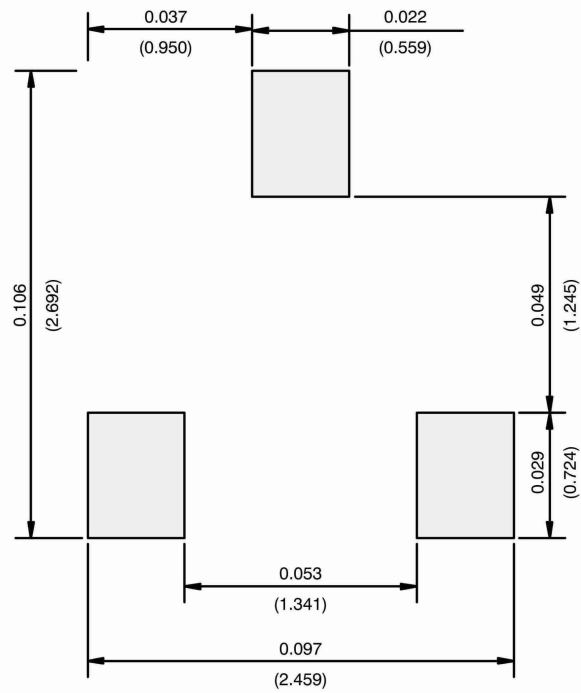
* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


SOT-23 (TO-236): 3-LEAD

Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	0.89	1.12	0.035	0.044
A₁	0.01	0.10	0.0004	0.004
A₂	0.88	1.02	0.0346	0.040
b	0.35	0.50	0.014	0.020
c	0.085	0.18	0.003	0.007
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E₁	1.20	1.40	0.047	0.055
e	0.95 BSC		0.0374 Ref	
e₁	1.90 BSC		0.0748 Ref	
L	0.40	0.60	0.016	0.024
L₁	0.64 Ref		0.025 Ref	
S	0.50 Ref		0.020 Ref	
q	3°	8°	3°	8°
ECN: S-03946-Rev. K, 09-Jul-01 DWG: 5479				

RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads
Dimensions in Inches/(mm)

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